

## Excellent Integrated System Limited

Stocking Distributor

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[IXYS Corporation](#)  
[DNA30E2200PA](#)

For any questions, you can email us directly:  
[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)

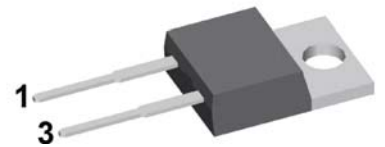
## High Voltage Standard Rectifier

$V_{RRM}$	=	2200V
$I_{FAV}$	=	30A
$V_F$	=	1.24V

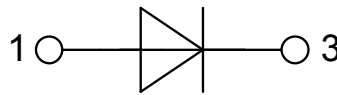
### Single Diode

Part number

**DNA30E2200PA**



Backside: anode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

#### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

#### Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

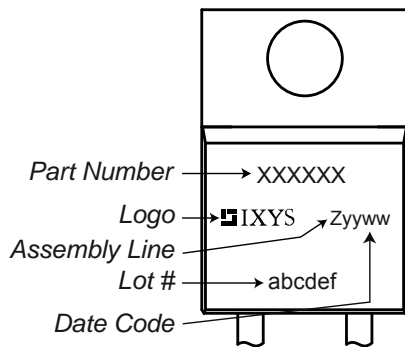
Rectifier				Ratings			Unit
Symbol	Definition	Conditions	min.	typ.	max.		
$V_{RSM}$	max. non-repetitive reverse blocking voltage				2300	V	
$V_{RRM}$	max. repetitive reverse blocking voltage				2200	V	
$I_R$	reverse current	$V_R = 2200\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		40	$\mu\text{A}$	
		$V_R = 2200\text{ V}$	$T_{VJ} = 150^\circ\text{C}$		1.5	mA	
$V_F$	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^\circ\text{C}$		1.26	V	
					1.53	V	
		$I_F = 60\text{ A}$	$T_{VJ} = 150^\circ\text{C}$		1.24	V	
					1.63	V	
$I_{FAV}$	average forward current	$T_C = 140^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ\text{C}$		30	A	
$V_{F0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^\circ\text{C}$		0.83	V	
$r_F$	slope resistance				13.4	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.7	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.50		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		210	W	
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		370	A	
					400	A	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$	$T_{VJ} = 150^\circ\text{C}$	315	A	
				$T_{VJ} = 150^\circ\text{C}$	340	A	
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		685	A <sup>2</sup> s	
					665	A <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$	$T_{VJ} = 150^\circ\text{C}$	495	A <sup>2</sup> s	
				$T_{VJ} = 150^\circ\text{C}$	480	A <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 700\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	7		pF	



# DNA30E2200PA

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			35	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g
$M_D$	mounting torque		0.4		0.6	Nm
$F_C$	mounting force with clip		20		60	N

### Product Marking



### Part number

- D = Diode
- N = High Voltage Standard Rectifier
- A = (>= 2000V)
- 30 = Current Rating [A]
- E = Single Diode
- 2200 = Reverse Voltage [V]
- PA = TO-220AC (2)

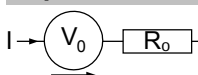
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DNA30E2200PA	DNA30E2200PA	Tube	50	507762

Similar Part	Package	Voltage class
DNA30E2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30EM2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30E2200FE	i4-Pac (2HV)	2200
DNA30E2200IY	TO-262 (2HV) (I2PAK)	2200

### Equivalent Circuits for Simulation

\* on die level

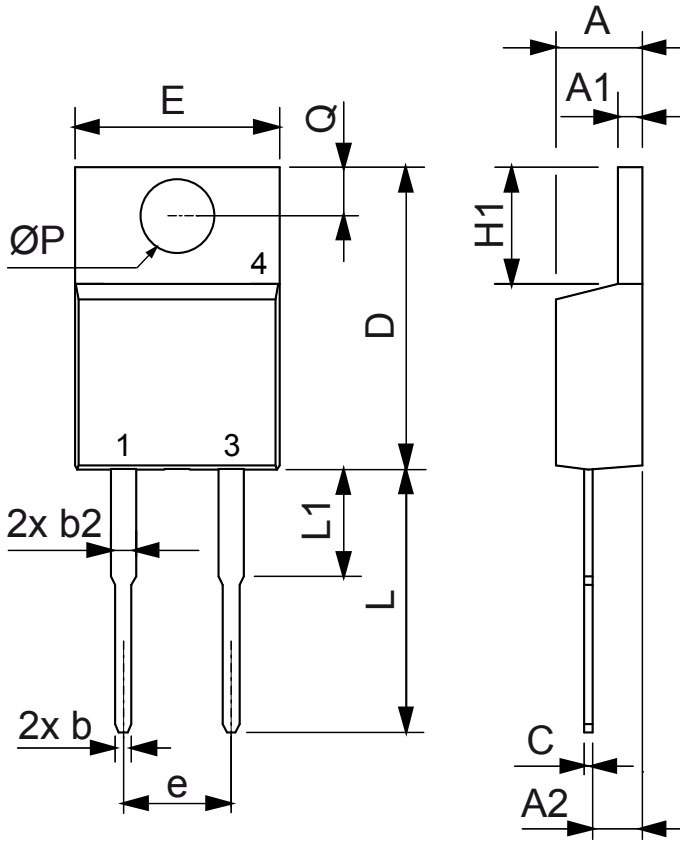
$T_{VJ} = 175\text{ °C}$



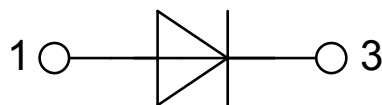
Rectifier

$V_{0\ max}$	threshold voltage	0.83	V
$R_{0\ max}$	slope resistance *	10.2	mΩ

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



**Rectifier**

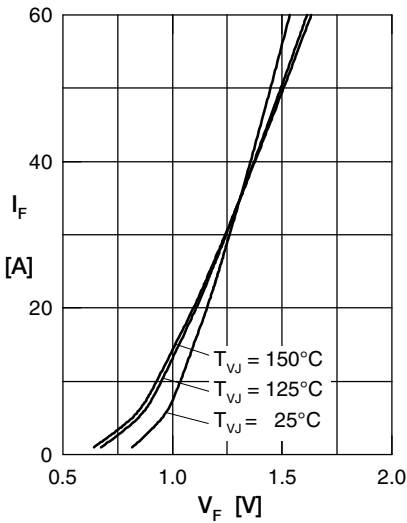


Fig. 1 Forward current versus voltage drop per diode

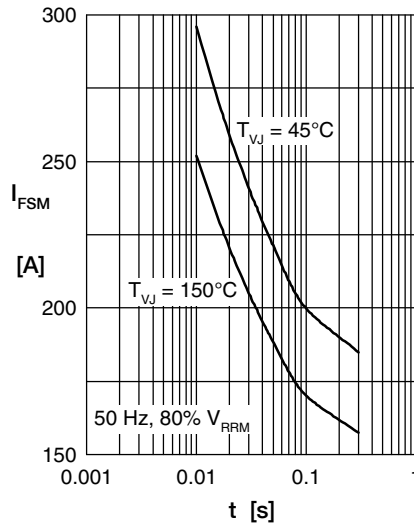


Fig. 2 Surge overload current

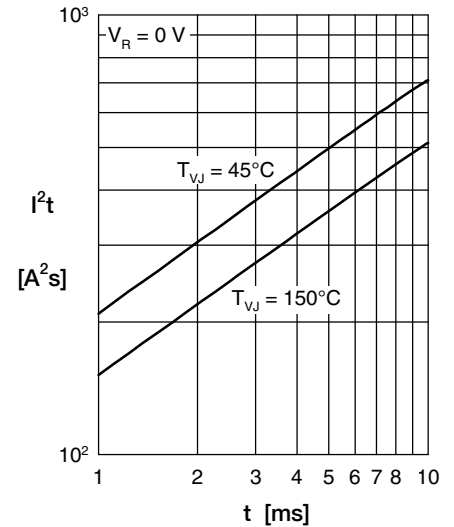


Fig. 3  $I^2t$  versus time per diode

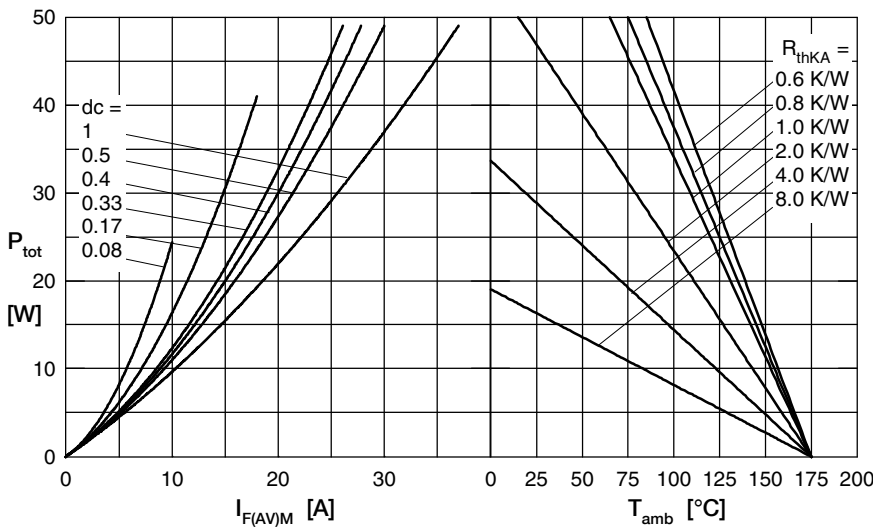


Fig. 4 Power dissipation versus direct output current and ambient temperature

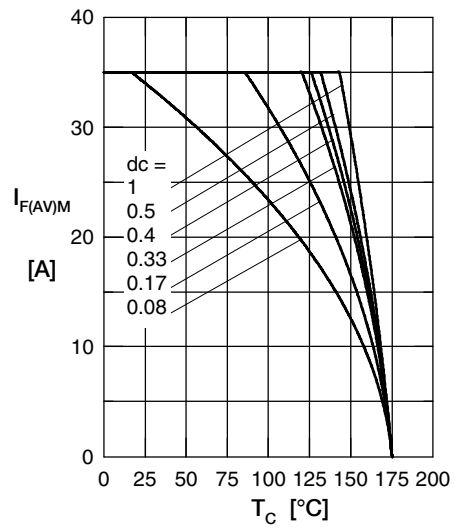


Fig. 5 Max. forward current versus case temperature

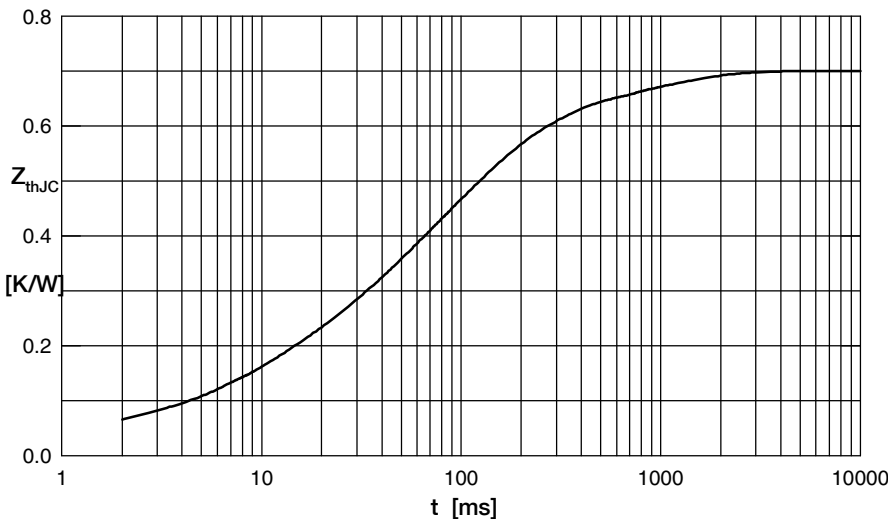


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.03	0.0003
2	0.072	0.0065
3	0.131	0.027
4	0.367	0.105
5	0.1	0.8